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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
09/993,492	11/27/2001	Hongyong Zhang	740756-2394	1546
22204 75	590 01/12/2004		EXAM	INER
NIXON PEABODY, LLP			KEBEDE, BROOK	
401 9TH STREET, NW SUITE 900		ART UNIT	PAPER NUMBER	
WASINGTON, DC 20004-2128			2823	
			DATE MAILED: 01/12/200	4

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	09/993,492	ZHANG ET AL.	
Office Action Summary	Examin r	Art Unit	
	Brook Kebede	2823	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet wi	th the correspondence address	
A SHORTENED STATUTORY PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO - Extensions of time may be available under the provisions of 37 CF after SIX (6) MONTHS from the mailing date of this communication - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory pe - Failure to reply within the set or extended period for reply will, by si - Any reply received by the Office later than three months after the meanned patent term adjustment. See 37 CFR 1.704(b). Status	DN. R 1.136(a). In no event, however, may a ron. a reply within the statutory minimum of thirteriod will apply and will expire SIX (6) MON tatute, cause the application to become AB	eply be timely filed y (30) days will be considered timely. THS from the mailing date of this communication. ANDONED (35 U.S.C. § 133).	
1) \boxtimes Responsive to communication(s) filed on $\underline{0}$	<u> 18 October 2003</u> .		
2a)⊠ This action is FINAL . 2b)☐ T	This action is non-final.		
3) Since this application is in condition for all closed in accordance with the practice und			
Disposition of Claims			
4) Claim(s) 1-32 is/are pending in the applica	tion.		
4a) Of the above claim(s) is/are with	drawn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-32</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction ar	nd/or election requirement.		
Application Papers			
9)☐ The specification is objected to by the Exar			
10)☐ The drawing(s) filed on is/are: a)☐	accepted or b) objected to	by the Examiner.	
Applicant may not request that any objection to	the drawing(s) be held in abeyar	nce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the co			
11) The oath or declaration is objected to by the	e Examiner. Note the attached	d Office Action or form PTO-152.	
Priority under 35 U.S.C. §§ 119 and 120			
12) Acknowledgment is made of a claim for for a) All b) Some * c) None of:	reign priority under 35 U.S.C.	§ 119(a)-(d) or (f).	
1. Certified copies of the priority docum	nents have been received.		
2. Certified copies of the priority docum	nents have been received in A		
3. Copies of the certified copies of the		received in this National Stage	
application from the International Bu * See the attached detailed Office action for a	• • • • • • • • • • • • • • • • • • • •	received	
13) Acknowledgment is made of a claim for dom			
since a specific reference was included in the			
37 CFR 1.78.	nrovicional analication has b	oon received	
 a) The translation of the foreign language 14) Acknowledgment is made of a claim for dom 			
reference was included in the first sentence			
Attachment(s)			
) Notice of References Cited (PTO-892)	4) Interview S	Summary (PTO-413) Paper No(s)	
2) D Notice of Draftsperson's Patent Drawing Review (PTO-948	5) Notice of I	nformal Patent Application (PTO-152)	
3) X Information Disclosure Statement(s) (PTO-1449) Paper No	o(s) . 6) Other:		

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DETAILED ACTION

Double Patenting

1. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

2. Claims 1-34 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-27 of U.S. Patent No. 5,403,772. Although the conflicting claims are not identical, they are not patentably distinct from each other because of the following reasons:

The claimed subject matter of the instant application, i.e., "A method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; first crystallizing the semiconductor film comprising silicon in an atmosphere comprising oxygen; and second crystallizing the semiconductor film comprising silicon in an atmosphere comprising hydrogen after the first crystallizing step," as recited in claim1, "A method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; first crystallizing the semiconductor film comprising silicon in an atmosphere comprising oxygen; and second crystallizing the semiconductor film comprising silicon in an atmosphere comprising nitrogen after the first

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crystallizing step," as recited in claim 6, "A method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; first crystallizing the semiconductor film comprising silicon in an atmosphere comprising oxygen; and second crystallizing, the semiconductor film comprising silicon in an atmosphere comprising hydrogen after the first crystallizing step, wherein each of the first and the second crystallizing steps is conducted at a temperature between 500 and 800°C," as recite in claim 11, "A method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; first crystallizing the semiconductor film comprising silicon in an atmosphere comprising oxygen; and second crystallizing -the semiconductor film comprising silicon in an atmosphere comprising nitrogen, wherein each of the first and the second crystallizing steps is conducted at a temperature between 500 and 800 °C," as recited in claim 16, "A method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; selectively forming a cover film over the semiconductor film comprising silicon; first crystallizing the semiconductor film comprising silicon in an atmosphere comprising oxygen; and second crystallizing the semiconductor film comprising silicon in an atmosphere comprising hydrogen, after the first crystallizing step" as recited in claim 21, and "A method of manufacturing a semiconductor device comprising the steps of forming a semiconductor film comprising silicon over a substrate; selectively forming a cover film over the semiconductor film comprising silicon; first crystallizing the semiconductor film comprising silicon in an atmosphere comprising oxygen; and second crystallizing the semiconductor film comprising silicon in an atmosphere comprising nitrogen after the first crystallizing step," as recited in claim 28, is claimed in claims 1-27 of U.S. Patent 5,403,772.

Furthermore, the claimed limitations of claims 2-5, 7-10, 12-15, 17-20, 22-27, and 29-34 within the scope of the claimed limitations in claims 1-27 of U.S. Patent 5,403,772.

Claims 2-5, 7-10, 12-15, 17-20, 22-27, and 29-34 also rejected as being dependent of the rejected independent base claims.

Response to Arguments

3. Applicants' arguments filed on October 8 2003 have been fully considered but they are not persuasive.

Applicants argued that "the '772 patent does not claim, for example, the particular order of crystallizing and the specific type of gas used in each crystallizing step as in Applicants' independent claims. Moreover, the dependent claims of the '772 patent further distinguish from Applicants' claimed invention with additional limitations that are not recited in Applicants' pending claim ..."

In response to the applicant's argument, the Examiner respectfully submits that such an argument is not commensurate with the scope of the claims, in particularly, as stated above. In addition, the Examiner respectfully submits that the added limitation, i.e., second crystallizing step is after second crystallizing step, is within the scope of Zhang et al. '772 patent. For example, see Claim 15 of Zhang et al. '772 patent. Claim 15 recites as follows:

"15. The method for manufacturing a semiconductor device according to claim
14 wherein said atmosphere is changed with time from one of oxygen, nitrogen
and hydrogen to another one of oxygen, nitrogen and hydrogen during said
seventh step."

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Since claim 15 being depending form claim 14, the first and second annealing step of the instant application claim is equivalent to the seven step of thermal annealing of Zhang et al. '772 patent. Thus, Zhang et al. '772 patent is broad enough cover the claimed invention of the instant application.

Furthermore, the transitional term "comprising", which is synonymous with "including," "containing," or "characterized by," is inclusive or open-ended and does not exclude additional, unrecited elements or method steps. See, e.g., Genentech, Inc. v. Chiron Corp., 112 F.3d 495, 501, 42 USPQ2d 1608, 1613 (Fed. Cir. 1997) ("Comprising" is a term of art used in claim language which means that the named elements are essential, but other elements may be added and still form a construct within the scope of the claim.); Moleculon Research Corp. v. CBS, Inc., 793 F.2d 1261, 229 USPQ 805 (Fed. Cir. 1986); In re Baxter, 656 F.2d 679, 686, 210 USPQ 795, 803 (CCPA 1981); Ex parte Davis, 80 USPQ 448, 450 (Bd. App. 1948).

Therefore, the rejection under judicially created doctrine of obviousness-type double patenting is still deemed proper.

Conclusion

4. Applicants' amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period

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will expire on the date the advisory action is mailed, and any extension fee pursuant to 37

CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event,

however, will the statutory period for reply expire later than SIX MONTHS from the date of this

final action.

Correspondence

5. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Brook Kebede whose telephone number is (703) 306-4511. The

examiner can normally be reached on 8-5 Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the

organization where this application or proceeding is assigned are (703) 308-7722 for regular

communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-0956.

BK

January 7, 2004

W. David Coleman

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Primary Examiner